

# **Wavelength Conversion and All-Optical Switching in QCL's.**

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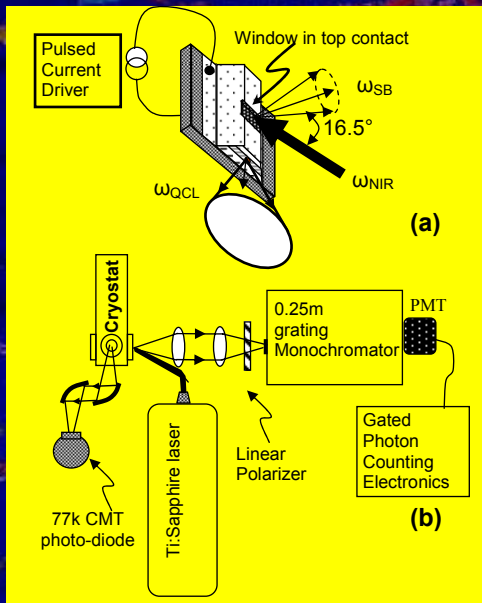


# Outline

- \*Device Design.
- \*Materials Considerations.
- \*Frequency mixing experiments.
- \* THz laser results.
- \*All-optical switching.
- \*Concluding Remarks.



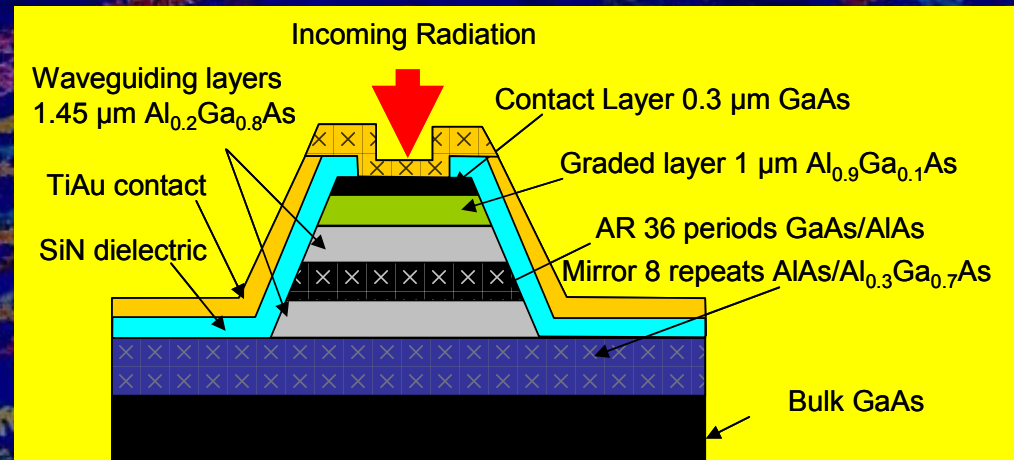
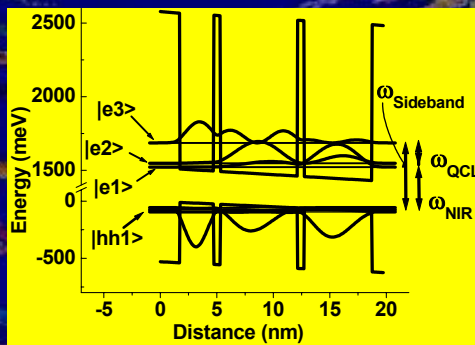
# Device Design



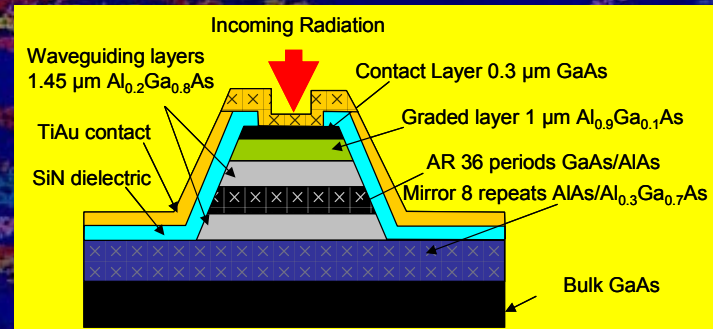
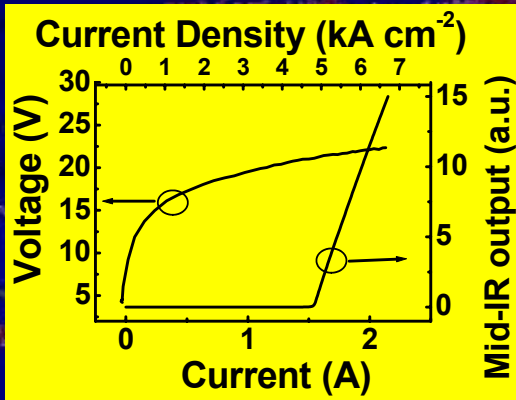
\*Standard (-ish) QCL with window in top contact

\* Needs cladding layers transparent to bandgap radiation

\* Needs DBR for reflective mode experiments.



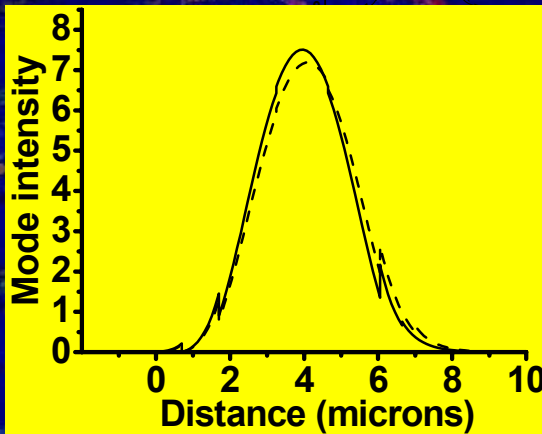
# Materials Issues



\* Lots of Al, but electrically stable.

\*  $J_{\text{Th}}$  indistinguishable from devices without holes or DBR's

\* DBR looks much like cladding to the QCL mode.



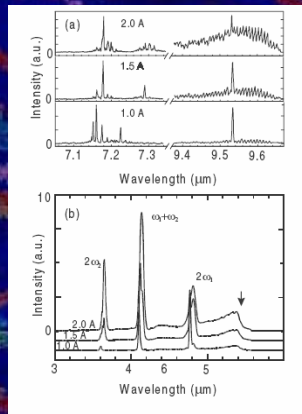
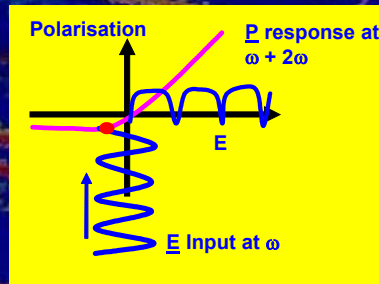
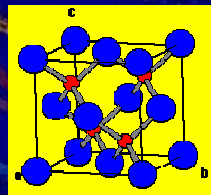


# Non-linear optics for new wavelengths

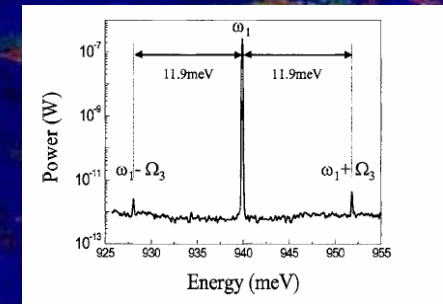
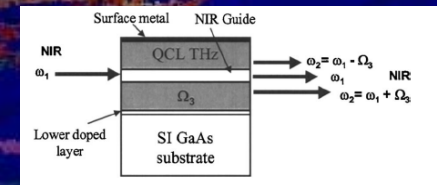
\*QCL cavities have high radiation density and the intrinsic  $\chi(2)$  of III-V's.

\*Artificial resonances can be designed-in.

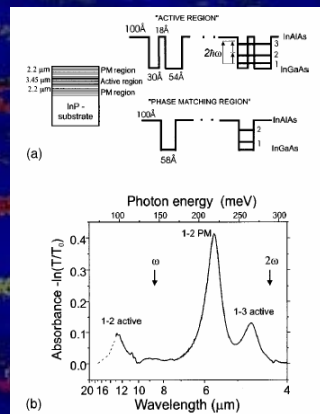
\*Designable dispersion for phase matching.



*N Owschinikow et al. PRL, 90 (4), 043902-1 (2003).*



*S S Dhillon et al. APL 87, 071101 (2005).*

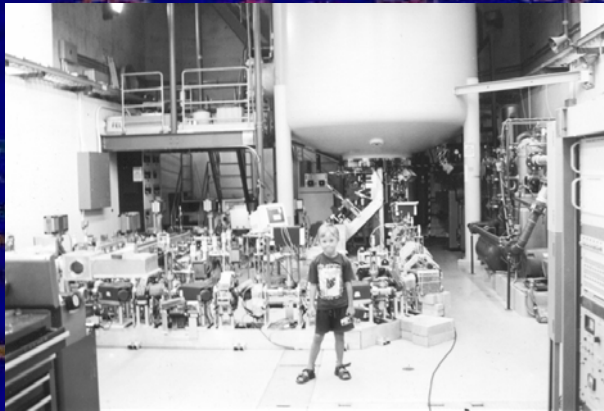
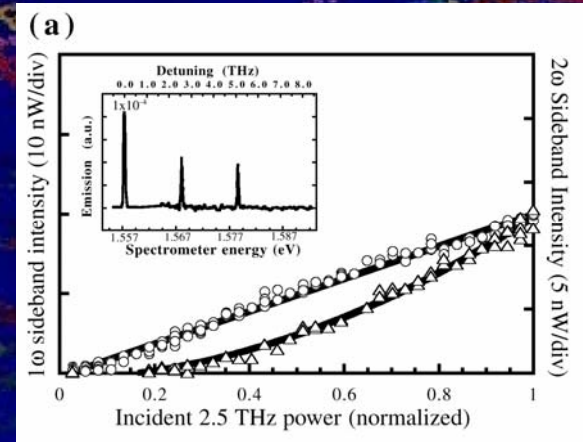
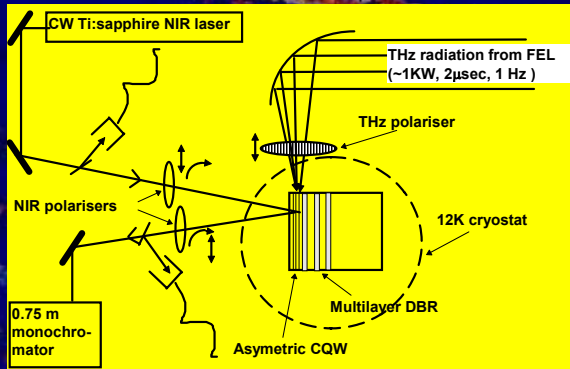


*K L Vodopyanov et al. APL 72(21), 2654 (1998).*

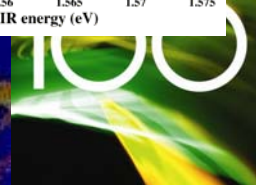
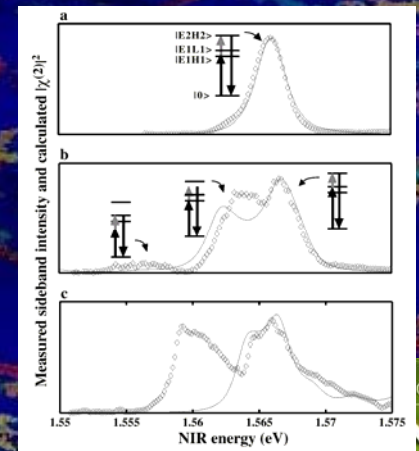
ITQW Ambleside Sept 2007.



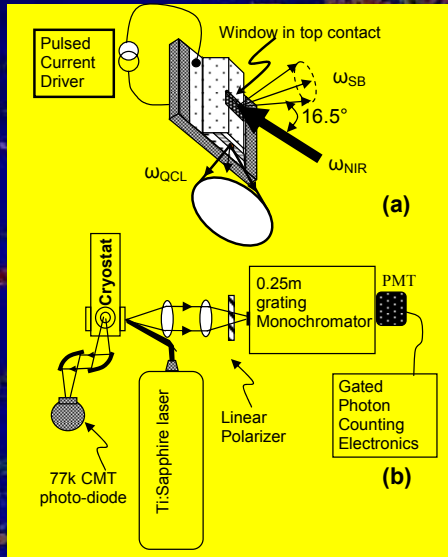
# Earlier FEL Experiments.



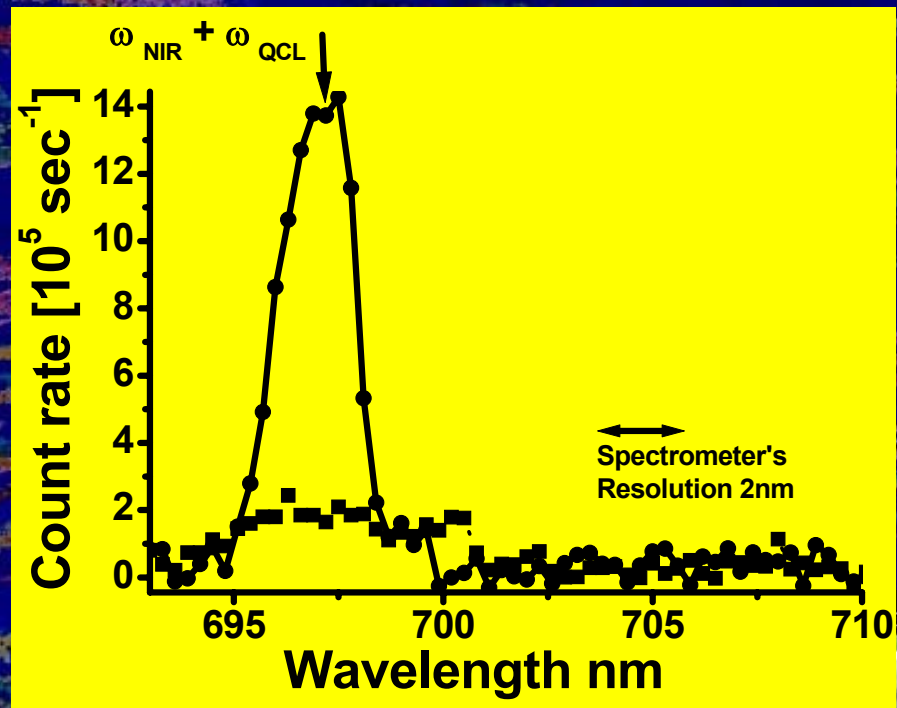
- \*Easy phase-matching.
- \*Polarisation insensitive.
- \*Broad bandwidth.
- \*telecomms  $\lambda$ 's



# Sideband spectra.



\*Gated measurement.





# THz lasers

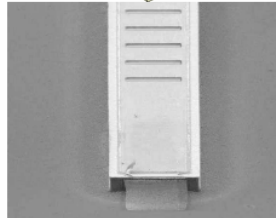
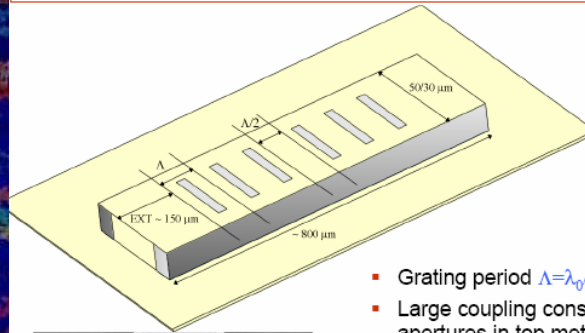
\* $\Delta\lambda/\lambda \sim 1\%$

\*Closer to DWFM applications.

\*Tunes over wide frequency range.

\*Polarisation insensitive.

## Surface emitting second order DFB lasers



- Grating period  $\Lambda = \lambda_0 / n_{\text{eff}}$  ( $\sim 30 \mu\text{m}$  for  $\sim 3 \text{ THz}$ )
- Large coupling constant  $\kappa$  obtained by having apertures in top metal
- Lithographically defined dry- etched facets to control phase of reflection at the facets
- Challenging fabrication
- Challenging design – higher order lateral modes need to be avoided

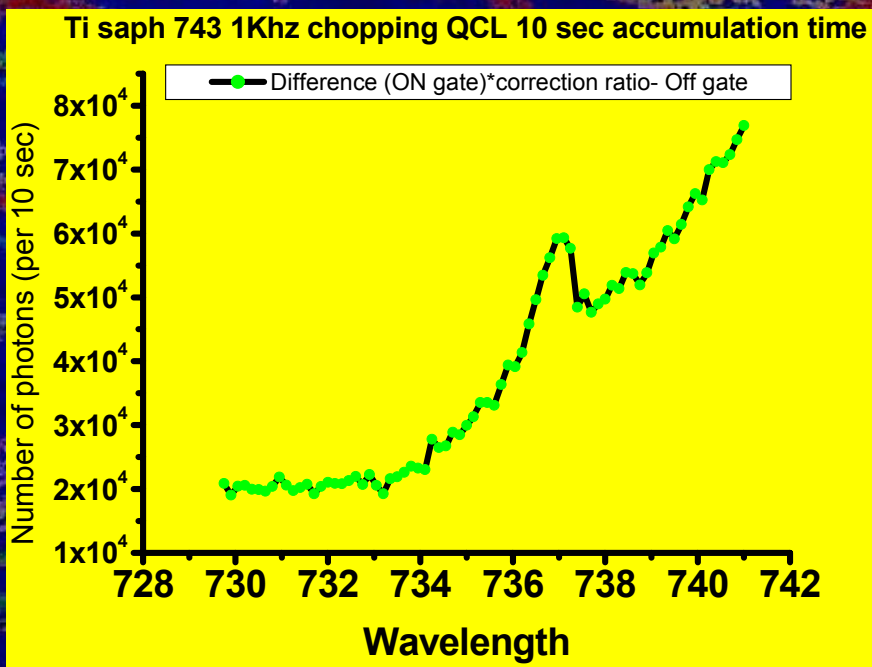


# Sideband generation in THz lasers

\* $\Delta\lambda/\lambda \sim 1\%$

\*Sideband has right polarisation dependence

\*Tunes over wide frequency range.



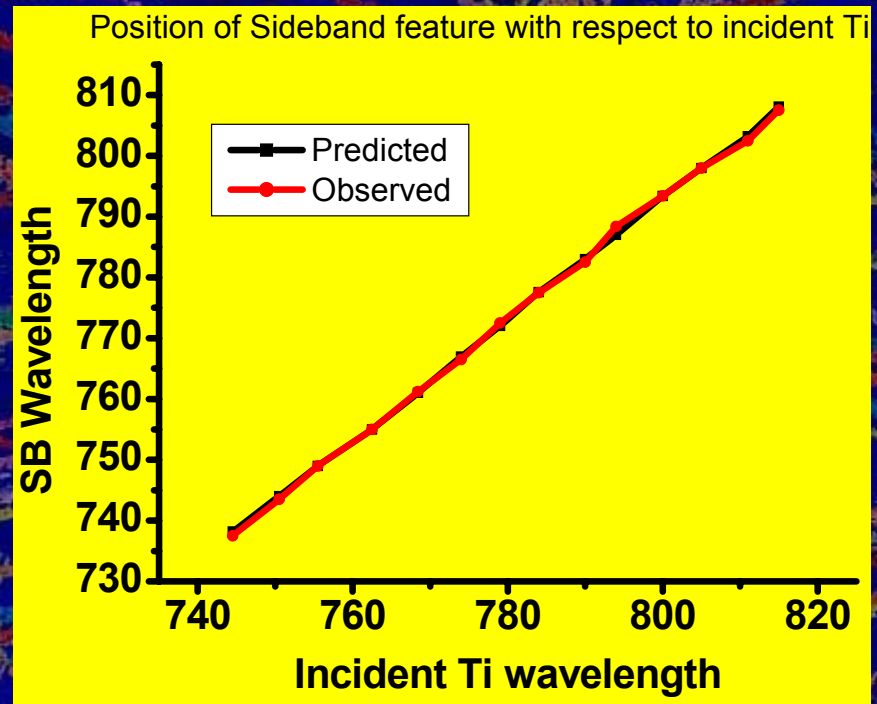


# Sideband tracks with incident wavelength.

\* $\Delta\lambda/\lambda \sim 1\%$

\*Sideband has right energy dependence

\*Tunes over wide frequency range.



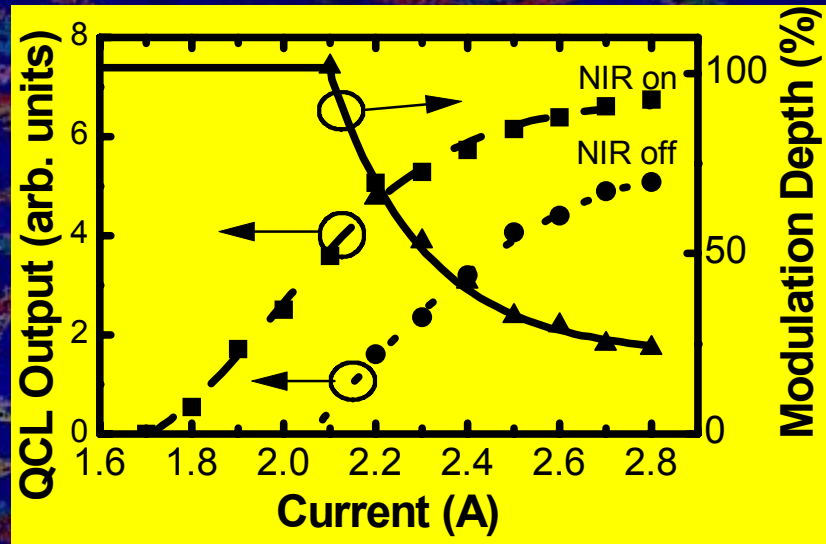


# All-optical switching.

\*Seen only in 25% Al samples.

\*QCL  $J_{th}$  lowers when Bandgap radiation is applied.

\*100% modulation depth possible @  $\sim$  50% of Max QCL o/p power.



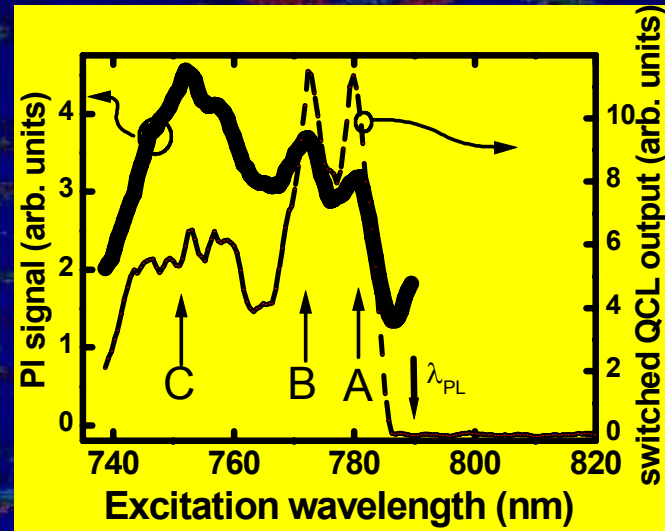


# Spectral Dependence.

\*Follows same spectral sensitivity as Active region PLE

\*QCL  $J_{th}$  lowers when Bandgap radiation is applied.

\*Implies switching effect originates with photoexcitation in AR.





# Switching dynamics.

- \*Even with PRF down to 200Hz, switching intensity is independent of pulse timings (!)
- \* Applying 10 nsec / 120 mW asynchronous pulses, need 13 to switch device for PRF's 10Hz-> 10kHz (!)
- \*Current pulse "resets" memory of NIR illumination.
- \*Re-timing function for telecomms.





# Switching Mechanism?

- \*Switching fluence  $6 \times 10^{10}$  photons, i.e  $\sim 2 \times$  electrons flowing in the 100 nsec J pulse.
- \* Could be J enhancement, but how come the long memory?
- \*Of 0, 10, 20, 25% Al clad devices , only 25% ones switched.
- \*Everything was below  $\sim 120\text{K}$  anyway

## Two possibilities



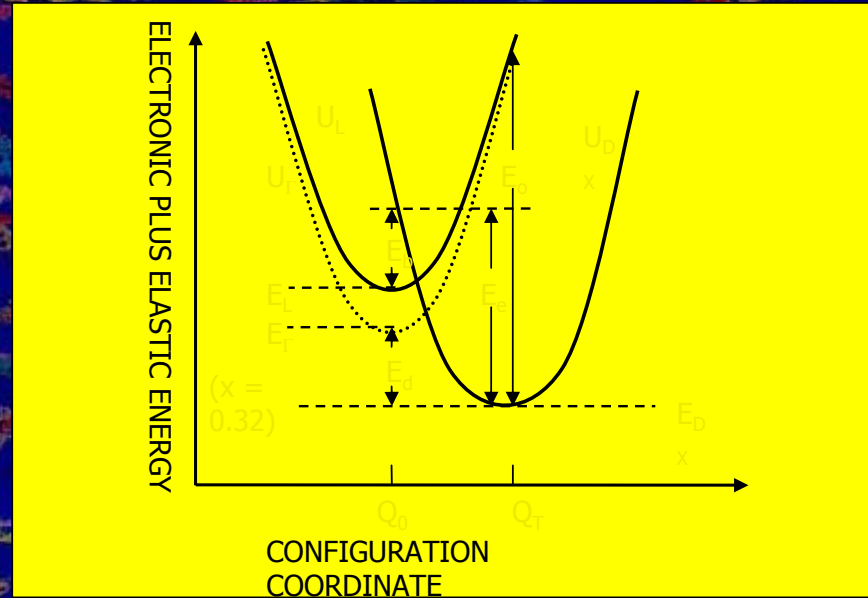
# DX centres in AlGaAs

\*  $\sim 10^9$  donors under window

\* Could hold  $\sim 1/2\%$  of switching charge

\* Would be field ionised by J pulse, with long recapture time?

\* Known to appear only at low T and  $x > 22\%$





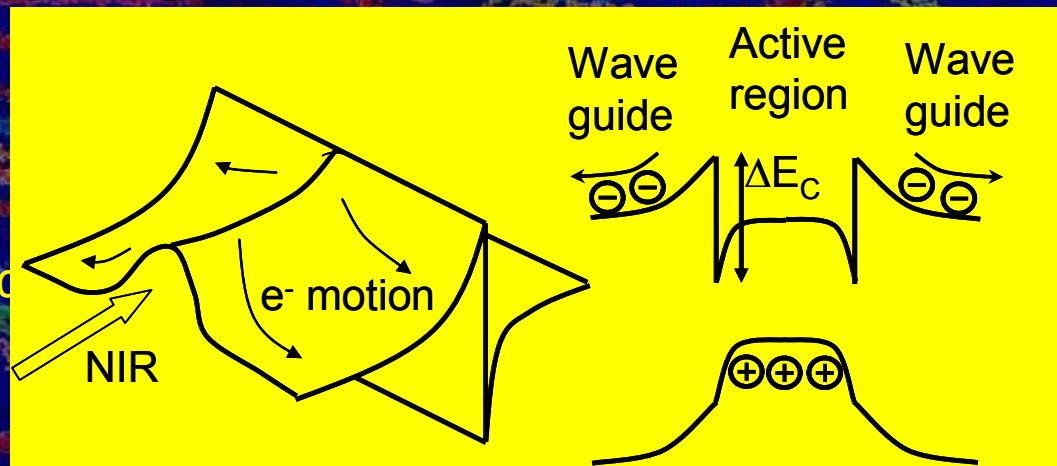
# Charge separation at heterojunction

\* Barrier only present for  $X \sim 20\%$  in clad

\* Needs "giant ambipolar" diffusion mechanism\* to spread charge.

\* Would work at high T and in InGaAs.

\* Watch this space....



\* See K H Gulden et al. PRL 66, 373 (1991).



# Concluding remarks

- \* NL frequency mixing demonstrated
- \* Electronically modulatable two-terminal device for a variety of telecoms functions. (add-drop, packet switching, high bandwidth, data transparent conversion etc.)
- \* Principles transferable to telecomms wavelengths.
- \* That elusive “killer application” for QCL’s?